

Amendments to the Claims:

The listing of claims will replace all prior versions and listings of claims in the application:

Listing of Claims:

- 5 1 (currently amended): A method for manufacturing a ternary nitride-based buffer layer of a nitride-based light-emitting device, comprising the steps of:
- providing a substrate;
- introducing a first reaction source comprising a first group III element into a chamber at a first temperature, wherein the first group III element is
- 10 deposited on the substrate; [[and]]
- introducing a second reaction source comprising a second group III element and a third reaction source comprising nitrogen into the chamber at a second temperature; and [[for]]
- forming a ternary nitride-based buffer layer ~~with~~ by reacting the second
- 15 group III element and the third reaction source with the first group III element on the substrate; [[,]]
- ~~where~~ wherein the first temperature is different from the second temperature.
- 2 2 (currently amended): The method of claim 1, wherein the substrate comprises at
- 20 least a material selected from the group consisting of sapphire, GaN, AlN, SiC, GaAs, GaP, Si, ZnO, MgO, MgAl₂O₄, and glass, ~~and the like~~.
- 3 3 (original): The method of claim 1, wherein the first temperature is 500°C or above.
- 25 4 (original): The method of claim 1, wherein the second temperature is 700°C or above.
- 5 5 (currently amended): The method of claim 1, wherein the first group III element comprises at least a material selected from the group consisting of Al, Ga, and In,
- 30 ~~and the like~~.

6 (currently amended): The method of claim 1, wherein the second group III element comprises at least a material selected from the group consisting of Al, Ga, and In, ~~and the like~~.

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7 (original): The method of claim 1, wherein the ternary nitride-based buffer layer thickness is between 1nm and 500nm.

8 (currently amended): The method of claim 1, wherein the ternary nitride-based
10 buffer layer comprises at least a material selected from the group consisting of InGaN, AlGaN, and InAlN, ~~and the like~~.

9-19 (cancelled).

15 20 (previously presented): The method of claim 1, wherein the melting point of the first group III element is lower than the first temperature.

21 (previously presented): The method of claim 1, wherein the second temperature is not lower than the melting point of the first group III element.

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22 (currently amended): A method for manufacturing a ternary nitride-based buffer layer of a nitride-based light-emitting device, comprising the steps of:
providing a substrate;
introducing a first reaction source comprising a first group III element into a
25 chamber, wherein the first group III element is deposited on the substrate;
and
subsequent to introducing the first reaction source into the chamber,
introducing a second reaction source comprising a second group III
element and a third reaction source comprising nitrogen into the
30 chamber;

forming a ternary nitride-based buffer layer by reacting the second group III element and the third reaction source to react with the first group III element on the substrate ~~for forming a ternary nitride-based buffer layer.~~

- 5 23 (previously presented): The method of claim 22, wherein the temperature of the step for introducing the first reaction source into the chamber is different from the temperature of the step for introducing the second reaction source and the third reaction source into the chamber.
- 10 24 (previously presented): The method of claim 23, wherein the melting point of the first group III element is lower than the temperature of introducing the first reaction source into the chamber.
- 15 25 (previously presented): The method of claim 23, wherein the temperature of introducing the second reaction source and the third reaction source into the chamber is not lower than the melting point of the first group III element.